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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION OF

LEE et al.

Appln. No.: 09/751,453

Filed: January 2, 2001



Confirmation No.: 7152

Group Art Unit: 2814

Examiner: Rao, Shrinivas H.

Title: METHOD OF FABRICATING CAPACITORS FOR SEMICONDUCTOR DEVICES

June 12, 2002

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AMENDMENT

Hon. Commissioner of Patents
Washington, D.C. 20231

RECEIVED
JUN 13 2002
TECHNOLOGY CENTER 2800

Sir:

In response to the Office Action dated March 13, 2002, please enter the following amendments and remarks:

IN THE SPECIFICATION:

Please replace the paragraph beginning on page 1, line 22 and ending on page 2, line 3 with the following new paragraph:

Accordingly, various methods of ensuring sufficient capacitance for DRAM capacitors have been proposed. For example, methods of increasing the area of a capacitor by modifying the physical structure of the capacitor to form a three-dimensional structure such as a cylinder or reducing the thickness of a dielectric film have been used until recently.

Please replace the paragraph beginning on page 2, line 4 with the following new paragraph:

Recently, research has also been conducted to provide a dielectric film having a NO (Nitride-Oxide) structure or an ONO (Oxide-Nitride-Oxide) structure in place of the conventional silicon oxide. Other alternative dielectric films that have been considered include Ta₂O₅ or BST (BaSrTiO₃) that ensure a high capacitance providing an increased dielectric constant (typically 20 to 25).